

Electronic Supporting Information

**B-doped 3C-SiC nanowires with finned microstructure for
efficient visible-light-driven photocatalytic hydrogen
production**

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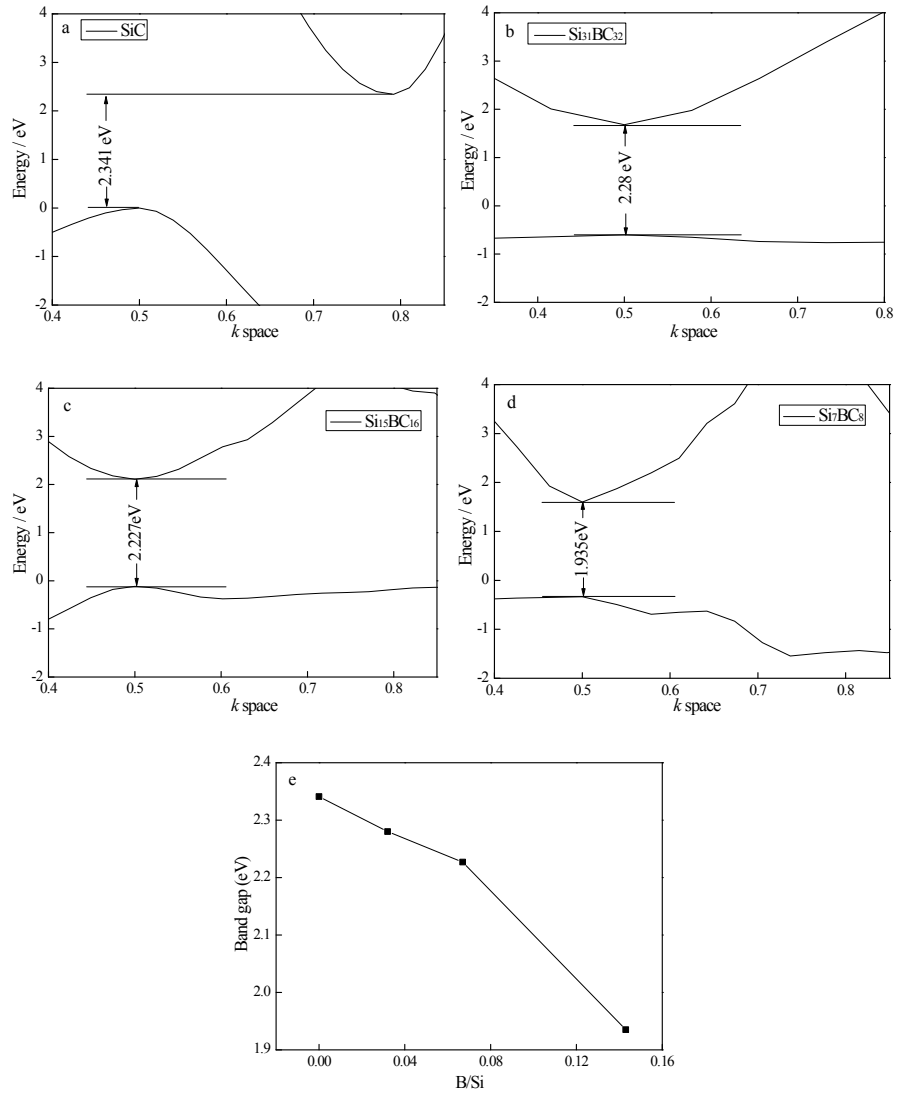
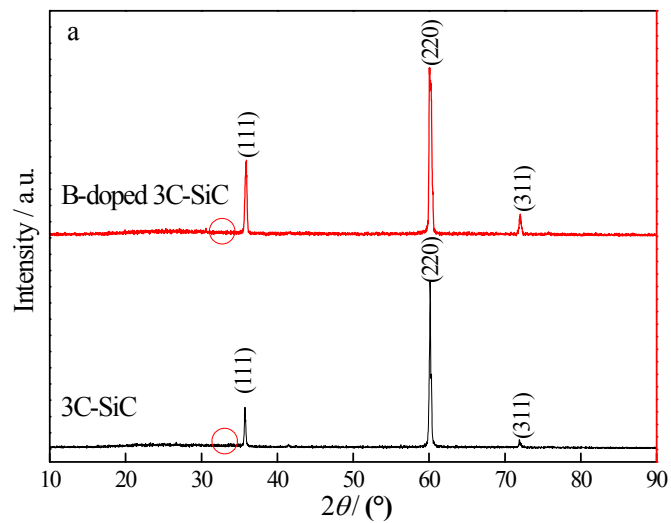


Fig. S1 (a)-(d) Calculated PDOS of 3C-SiC and B-doped 3C-SiC including $\text{Si}_{31}\text{BC}_{32}$, $\text{Si}_{15}\text{BC}_{16}$ and Si_7BC_8 , (e) is the band gap of $\text{Si}_{n-1}\text{BC}_n$ ($n=8, 16, 32$).



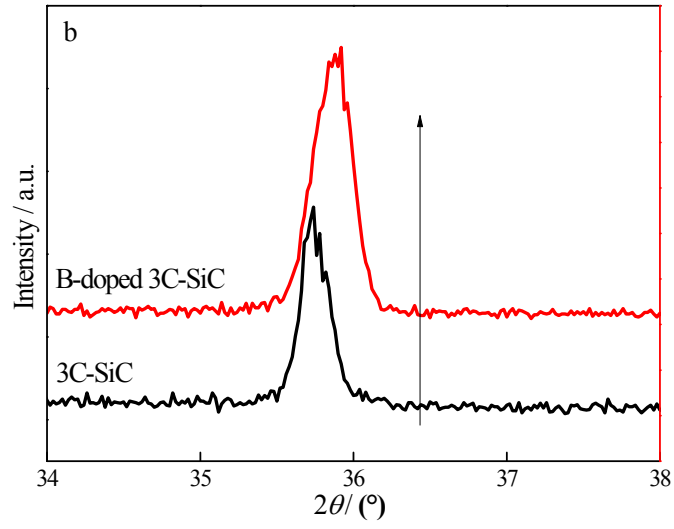
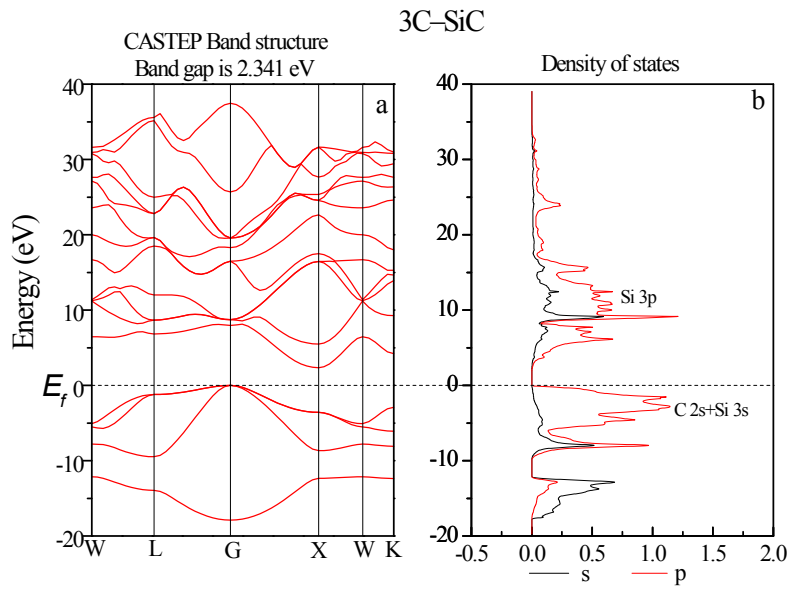


Fig. S2. XRD patterns of the as-prepared (a) and the magnification of the diffraction peak (111) (b)



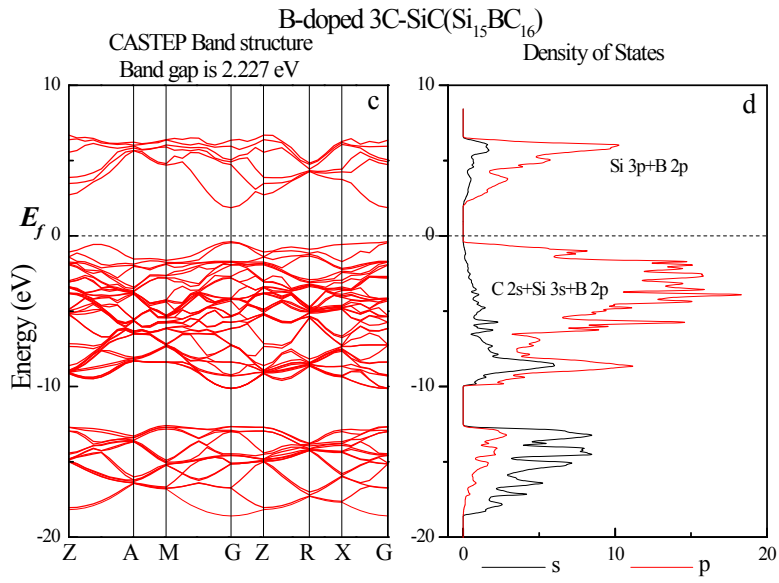
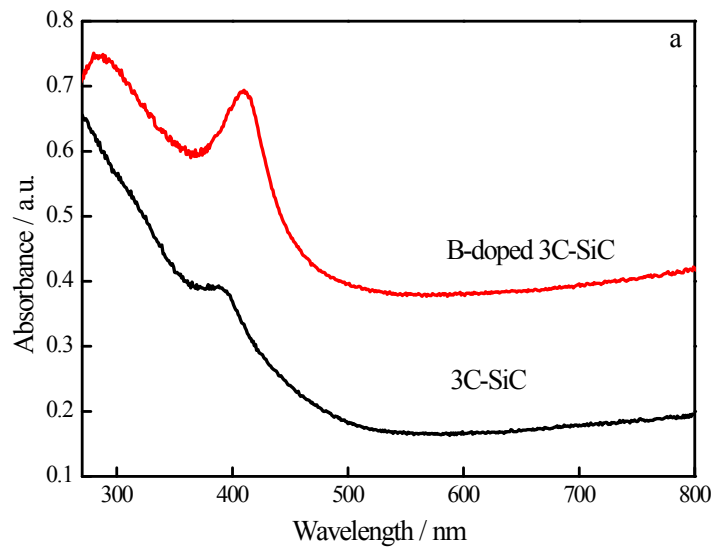


Fig. S3. The calculated energy band and density of states (DOS) of pure 3C-SiC (a and b) and B-doped 3C-SiC (c and d)



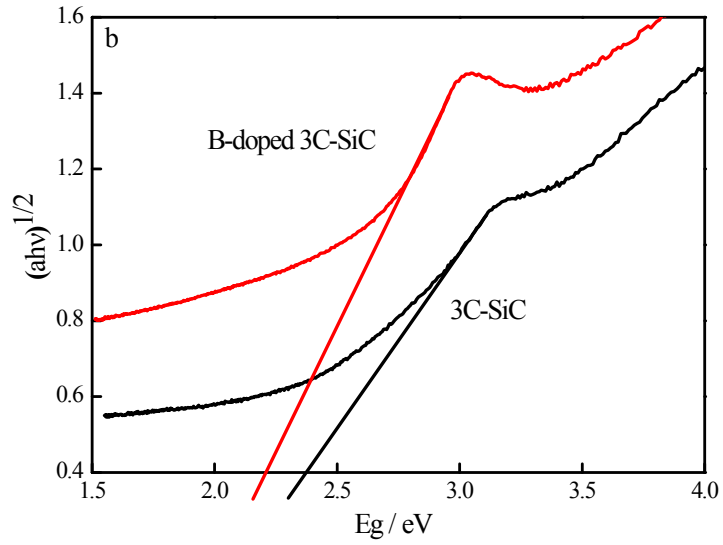


Fig. S4. (a) UV-Vis diffusion reflectance spectra (b) The plots of $(\alpha hv)^{1/2}$ versus $h\nu$. The bandgap of the samples

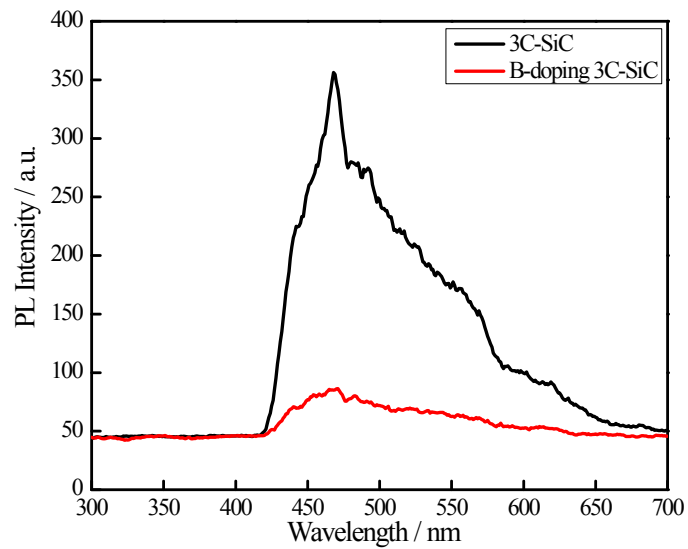


Fig. S5 Photoluminescence spectra of 3C-SiC and B-doped 3C-SiC.

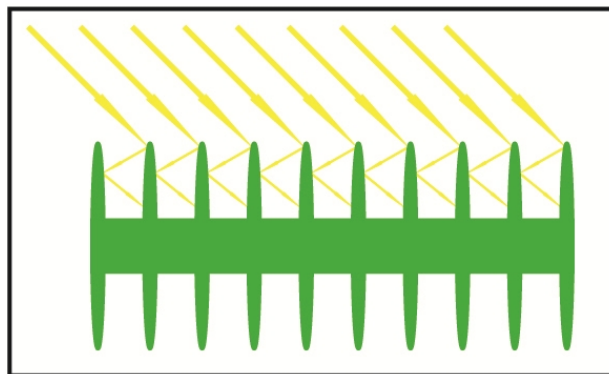
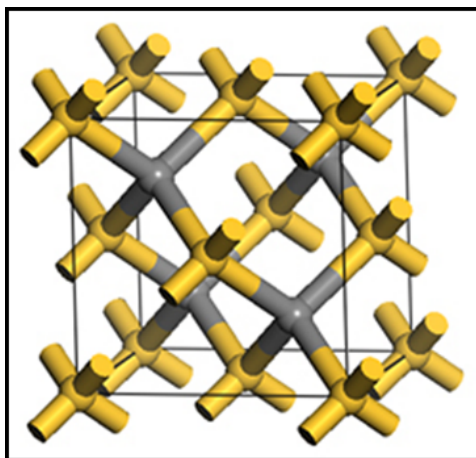


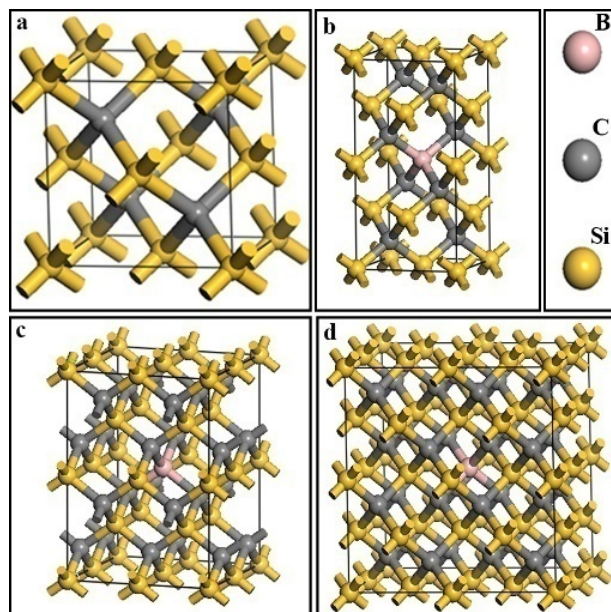
Fig. S6 Light reflection models in the B-doped 3C-SiC nanowires.

Table S1 Calculation conditions for geometry optimization and energy task

Task: Geometry optimization		Energy	
Functional	GGA PW91	LDA CA-PZ ^{1,2}	
Minimizer	Fine quality	-	
	Energy:	1.0e-5 eV/atom	-
	Max force:	0.03 eV/Å	-
	Max stress:	0.05 GPa	-
	Max displacement:	0.001 Å	-
Algorithm	BFGS:	use line search	-
Stress	0 for all	-	
Energy cutoff	700 eV	700 eV	
SCF tolerance	1.0*10 ⁻⁶ eV/atom	1.0*10 ⁻⁶ eV/atom	
Pseudopotentials	Ultrasoft ³	Norm-conserving ⁴	
FFT grid density	Fine quality	Standard	
Finite basis correction	Smart	Smart	
Electronic minimizer	Density Mixing	Density Mixing	
Orbital occupancy	Fixed	Fixed	
<i>k</i> point quality	Fine quality	Fine quality	
Band structure	Unchecked	Checked	Fine quality k point set
Density of states	Unchecked	Checked	Medium quality k point set



Scheme 1. 3C-SiC with a zinc blende structure



Scheme 2. Structures of calculation models

References

- 1 D. M. Ceperley and B. J. Alder, Phys. Rev. Lett., 1980, 45, 566-569.
- 2 J. P. Perdew, A. Zunger, J. P. Perdew and A. Zunger, Phys. Rev. B, 1981, 23, 5048-5079.
- 3 D. Vanderbilt, Phys. Rev. B, 1990, 41, 7892-7895.
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